

ABSTRACT

A semiconductor device and method for fabricating the same are provided. The semiconductor device includes a substrate, a first active pattern disposed on the substrate and spaced apart from the substrate, a gate insulating film which surrounds the first active pattern, a first work function adjustment film which surrounds the gate insulating film and includes carbon, and a first barrier film which surrounds the first work function adjustment film, in which a carbon concentration of the first work function adjustment film increases as it goes away from the first barrier film.

FIG. 4